



C2M0280120D Information



For Reference Only

Part Number C2M0280120D **Manufacturer** Cree/Wolfspeed

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1200V 10A TO-247-3

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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C2M0280120D Specifications

Manufacturer Part Number C2M0280120D Manufacturer Cree/Wolfspeed Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series Z-FET? FET Type N-Channel Technology SiCFET (Silicon Carbide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 20V Vgs(th) (Max) @ Id 2.8V @ 1.25mA (Typ) Gate Charge (Qg) (Max) @ Vgs 20.4nC @ 20V Input Capacitance (Ciss) (Max) @ Vds 259pF @ 1000V Vgs (Max) +25V, -10V FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 370 mOhm @ 6A, 20V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series Z-FET? FET Type N-Channel Technology Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1209V Vgs(th) (Max) @ Vgs 1204	Manufacturer Part Number	C2M0280120D
Package TO-247-3 Series Z-FET? FET Type N-Channel Technology SiCFET (Silicon Carbide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 20V Vgs(th) (Max) @ Id 2.8V @ 1.25mA (Typ) Gate Charge (Qg) (Max) @ Vgs 20.4nC @ 20V Input Capacitance (Ciss) (Max) @ Vds 259F @ 1000V Vgs (Max) +25V, -10V FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 370 mOhm @ 6A, 20V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Manufacturer	Cree/Wolfspeed
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FET TypeN-ChannelTechnologySiCFET (Silicon Carbide)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)20VVgs(th) (Max) @ Id2.8V @ 1.25mA (Typ)Gate Charge (Qg) (Max) @ Vgs20.4nC @ 20VInput Capacitance (Ciss) (Max) @ Vds259pF @ 1000VVgs (Max)+25V, -10VFET Feature-Power Dissipation (Max)62.5W (Tc)Rds On (Max) @ Id, Vgs370 mOhm @ 6A, 20VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Package	TO-247-3
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 10A (Tc) 10A (Typ)	Technology	SiCFET (Silicon Carbide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 2.8V @ 1.25mA (Typ) Gate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds Vgs (Max) Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 370 mOhm @ 6A, 20V Operating Temperature Copyright Through Hole Supplier Device Package TO-247-3 Package / Case Pass Qu (1.25mA (Typ) 2.8V @ 1.25mA	Drain to Source Voltage (Vdss)	1200V
Vgs(th) (Max) @ Id 2.8V @ 1.25mA (Typ) Gate Charge (Qg) (Max) @ Vgs 20.4nC @ 20V Input Capacitance (Ciss) (Max) @ Vds 259pF @ 1000V Vgs (Max) +25V, -10V FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 370 mOhm @ 6A, 20V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Current - Continuous Drain (Id) @ 25°C	10A (Tc)
Gate Charge (Qg) (Max) @ Vgs 20.4nC @ 20V Input Capacitance (Ciss) (Max) @ Vds 259pF @ 1000V Vgs (Max) +25V, -10V FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 370 mOhm @ 6A, 20V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	20V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +25V, -10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 370 mOhm @ 6A, 20V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Vgs(th) (Max) @ Id	2.8V @ 1.25mA (Typ)
Vgs (Max) +25V, -10V FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 370 mOhm @ 6A, 20V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Gate Charge (Qg) (Max) @ Vgs	20.4nC @ 20V
FET Feature - Power Dissipation (Max) 62.5W (Tc) Rds On (Max) @ Id, Vgs 370 mOhm @ 6A, 20V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	259pF @ 1000V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Vgs (Max)	+25V, -10V
Rds On (Max) @ Id, Vgs370 mOhm @ 6A, 20VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Power Dissipation (Max)	62.5W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	370 mOhm @ 6A, 20V
Supplier Device Package TO-247-3 Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247-3
Report errors?	Package / Case	TO-247-3
		Report errors?

C2M0280120D Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

C2M0280120D Payment Methods



















C2M0280120D Shipping Methods













If you have any question about C2M0280120D, please do not hesitate to contact us!

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